

HiPerFET™

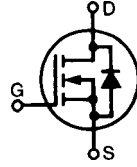
Power MOSFETs

IXFH 26N60/IXFT 26N60
IXFK 28N60

N-Channel Enhancement Mode

Avalanche Rated, High dv/dt, Low t_{rr}

Preliminary data

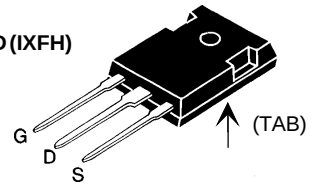


V_{DSS}	I_{D25}	$R_{DS(on)}$
600 V	26 A	0.25 Ω
600 V	28 A	0.25 Ω

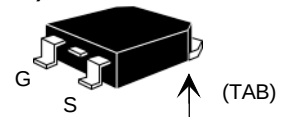
$t_{rr} \leq 250$ ns

Symbol	Test Conditions	Maximum Ratings		
		IXFH/ IXFT	IXFK	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	600	600	V
V_{GS}	Continuous	± 20	± 20	V
V_{GSM}	Transient	± 30	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$, Chip capability	26	28	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	104	112	A
I_{AR}	$T_C = 25^\circ\text{C}$	26	28	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	416	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	0.9/6	Nm/lb.in.
Weight		6	10	g

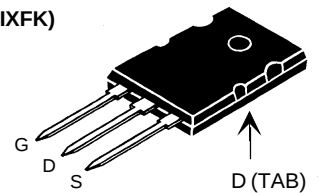
TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



TO-264 AA (IXFK)



G = Gate

S = Source

TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			± 200 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0$ V			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300$ μs , duty cycle $d \leq 2$ %			0.25 Ω

Features

- International standard packages
- Epoxy meet UL94V-0, flammability classification
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 • I _{D25} , pulse test	11	18	S
C_{iss}	} V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	5000		pF
C_{oss}		600		pF
C_{rss}		250		pF
t_{d(on)}	} V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 1.5 Ω (External),	30		ns
t_r		43		ns
t_{d(off)}		110		ns
t_f		30		ns
Q_{g(on)}	} V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}	250		nC
Q_{gs}		33		nC
Q_{gd}		115		nC
R_{thJC}	26N60		0.35	K/W
	28N60		0.30	K/W
R_{thCK}	TO-247		0.25	K/W
	TO-264		0.15	K/W

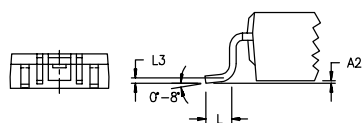
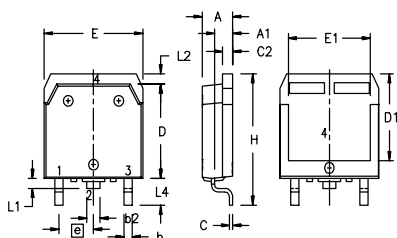
Source-Drain Diode

Characteristic Values

($T_1 = 25^\circ\text{C}$, unless otherwise specified)

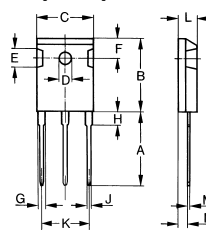
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	26N60 28N60		26 A 28 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	26N60 28N60		104 A 112 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr} Q_{RM} I_{RM}	$I_F = I_S$ -di/dt = 100 A/ μs , $V_R = 100\text{ V}$		1 10	250 ns μC A

TO-268AA (D³ PAK)



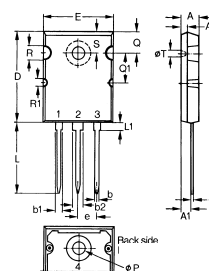
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	.025 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

TO-247 AD (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-264 AA (IXFK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Min. Recommended Footprint

